

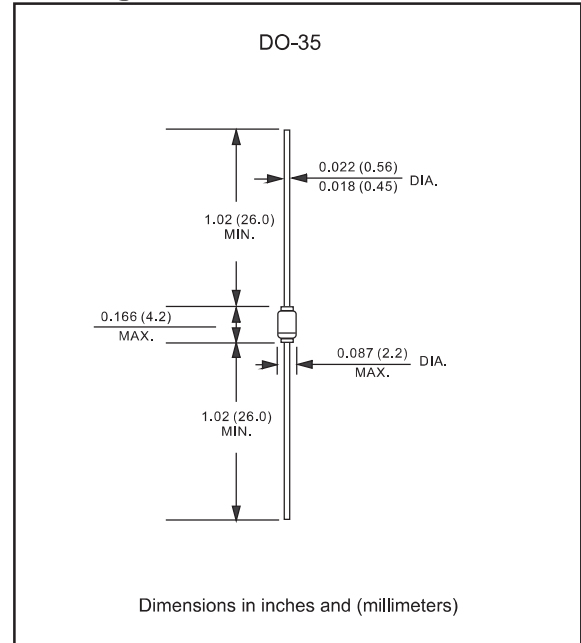
Features

- Axial lead type devices for through hole design
- Fast speed switching
- Silicon epitaxial planar chip structure
- Hermetically sealed glass
- Lead-free parts meet RoHS requirements

Mechanical data

- Case : Glass, DO-35
- Lead : Axial leads, solderable per MIL-STD-202, Method 208 guaranteed
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.125 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Repetitive peak reverse voltage		VRRM			100	V
Reverse voltage		VR			75	V
Peak forward surge current	tp=1μs	IFSM			2.0	A
Repetitive peak forward current		IFRM			500	mA
Forward continuous current		IF			300	mA
Average forward current		IF(AV)			150	mA
Power dissipation		PD			500	mW
Operating junction temperature range		TJ	-55		+150	°C
Storage temperature range		TSTG	-55		+150	°C

Electrical characteristics (AT $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage	IF=10mA	VF		0.86	1.00	V
Reverse current	VR=20V	IR			25	nA
	VR=20V, TJ=150°C	IR			50	μA
	VR=75V	IR			5.0	μA
Breakdown voltage	IR=100μA, tp/T=0.01, tp=0.3ms	V(BR)	100			V
Diode capacitance	VR=0V, f=1MHz, VHF=50mV	CD			4.0	pF
Rectification efficiency	VHF=2V, f=100MHz	ηr	45			%
Reverse recovery time	IF=IR=10mA, IRR=1mA	trr			8.0	ns
	IF=10mA, VR=6V, IRR=0.1 X IR, RL=100Ω	trr			4.0	ns

Rating and characteristic curves

FIG.1-TYPICAL FORWARD CHARACTERISTICS

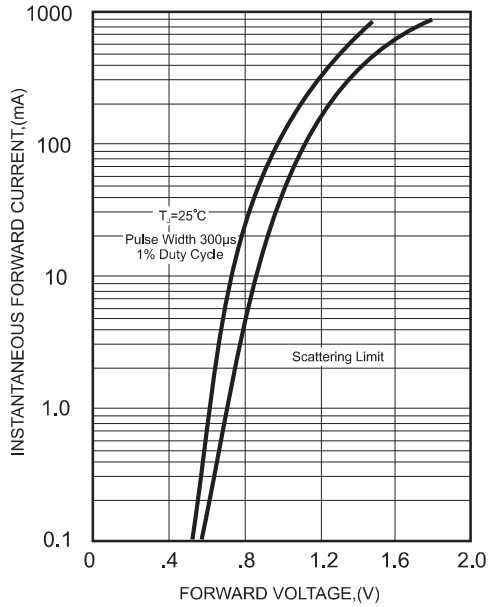


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

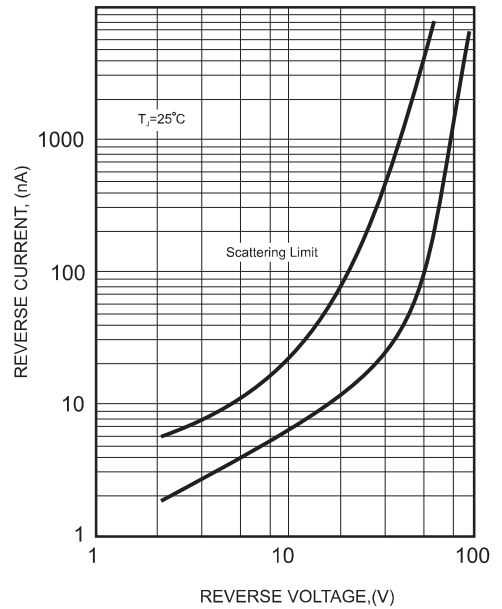


FIG.2 - TYPICAL DIODE CAPACITANCE

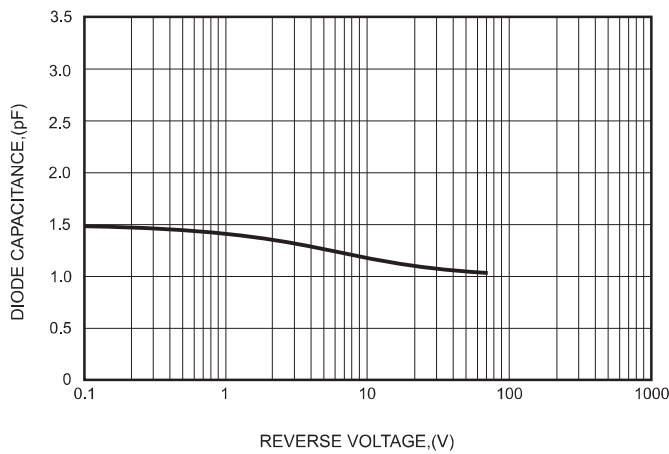


FIG.4 - REVERSE CURRENT VS. JUNCTION TEMPERATURE

